



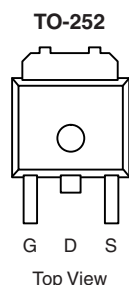
## N-Channel 60-V (D-S) 175 °C MOSFET

## PRODUCT SUMMARY

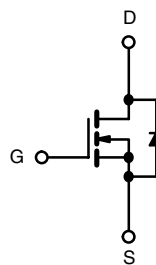
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>c</sup>	$Q_g$ (Typ)
60	0.0078 at $V_{GS} = 10$ V	93	94

## FEATURES

- TrenchFET<sup>®</sup> Power MOSFET
- 175 °C Junction Temperature
- 100 %  $R_g$  Tested
- High Threshold at High Temperature

RoHS  
COMPLIANT

Drain Connected to Tab



N-Channel MOSFET

Ordering Information: SUD50N06-08H0-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS  $T_A = 25$  °C, unless otherwise noted

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V <sub>DS</sub>	60	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 25 °C	I <sub>D</sub>	93 <sup>c</sup>	A
	T <sub>C</sub> = 125 °C		54 <sup>c</sup>	
Pulsed Drain Current		I <sub>DM</sub>	100	
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	91 <sup>c</sup>	
Avalanche Current, Single Pulse		I <sub>AS</sub>	50	
Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	125	mJ
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	136 <sup>b</sup>	W
	T <sub>A</sub> = 25 °C		3 <sup>a</sup>	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C

## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	$t \leq 10$ sec 15	18	°C/W
		Steady State 40	50	
Junction-to-Case	$R_{thJC}$	0.85	1.1	

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

b. See SOA curve for voltage derating.

c. Calculate continuous current based on maximum allowable junction temperature when using infinite heat sink. Package limitation current is 50 A.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ <sup>a</sup>	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	3.4		4.5	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 60\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ }^{\circ}\text{C}$			50	
		$V_{DS} = 60\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 175\text{ }^{\circ}\text{C}$			250	
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}$ , $V_{GS} = 10\text{ V}$	50			A
Drain-Source On-State Resistance <sup>b</sup>	$r_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 20\text{ A}$		0.0065	0.0078	$\Omega$
		$V_{GS} = 10\text{ V}$ , $I_D = 20\text{ A}$ , $T_J = 125\text{ }^{\circ}\text{C}$			0.013	
		$V_{GS} = 10\text{ V}$ , $I_D = 20\text{ A}$ , $T_J = 175\text{ }^{\circ}\text{C}$			0.0156	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}$ , $I_D = 20\text{ A}$		25		S
Dynamic <sup>a</sup>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $F = 1\text{ MHz}$		7000		pF
Output Capacitance	$C_{oss}$			450		
Reverse Transfer Capacitance	$C_{rss}$			240		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	0.75	1.5	2.3	$\Omega$
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 30\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 50\text{ A}$		94	145	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			35		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			20		
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 30\text{ V}$ , $R_L = 0.6\text{ }\Omega$ $I_D \cong 50\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 2.5\text{ }\Omega$		28	45	ns
Rise Time <sup>c</sup>	$t_r$			13	20	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			50	75	
Fall Time <sup>c</sup>	$t_f$			10	15	
Source-Drain Diode Ratings and Characteristics ( $T_C = 25\text{ }^{\circ}\text{C}$ )						
Pulsed Current	$I_{SM}$				100	A
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	$I_F = 50\text{ A}$ , $V_{GS} = 0\text{ V}$		1.0	1.5	V
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 50\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$		45	70	ns

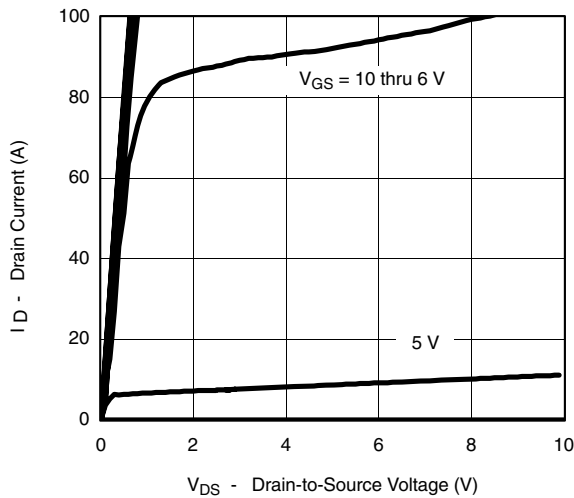
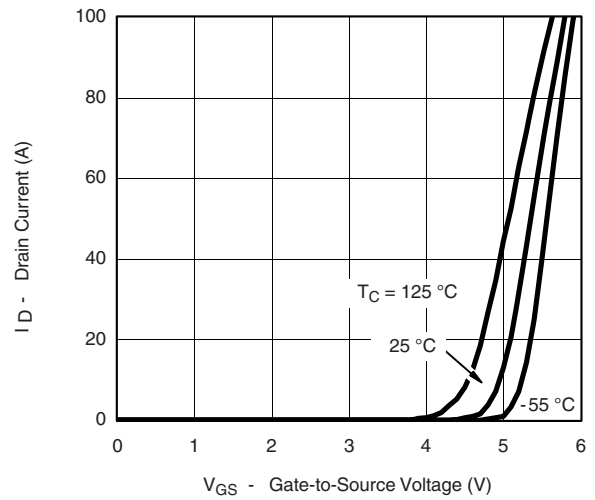
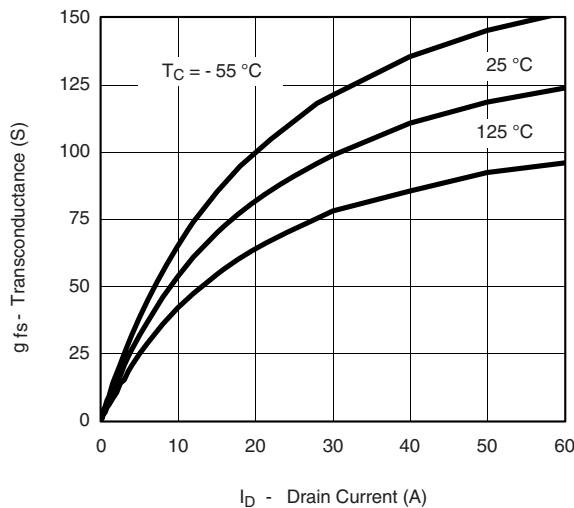
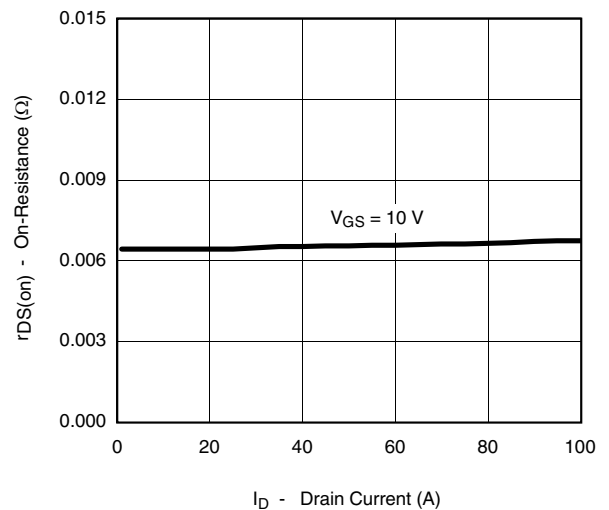
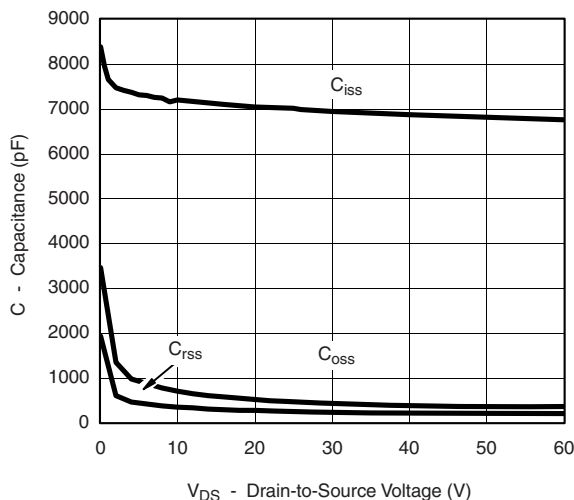
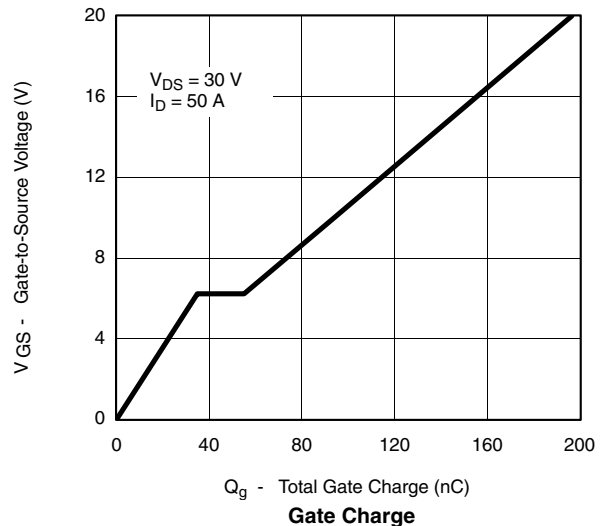
## Notes:

a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

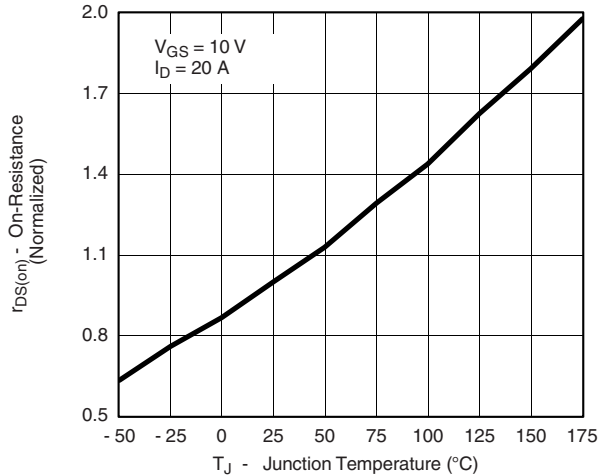
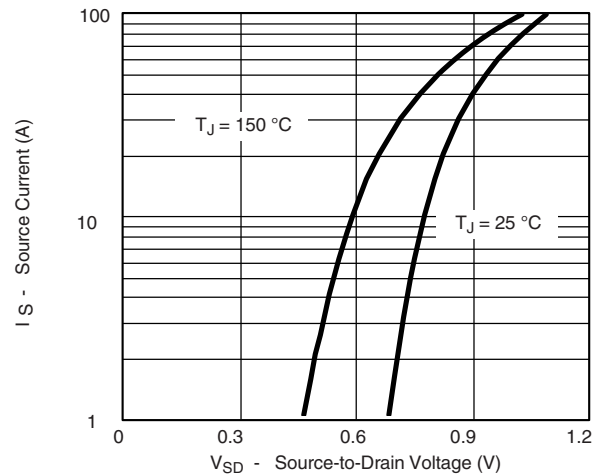
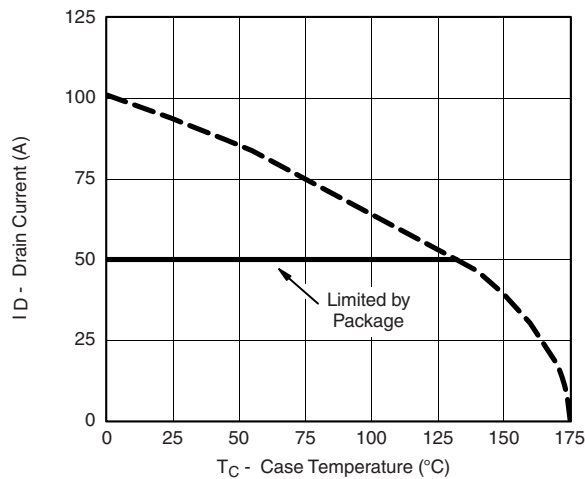
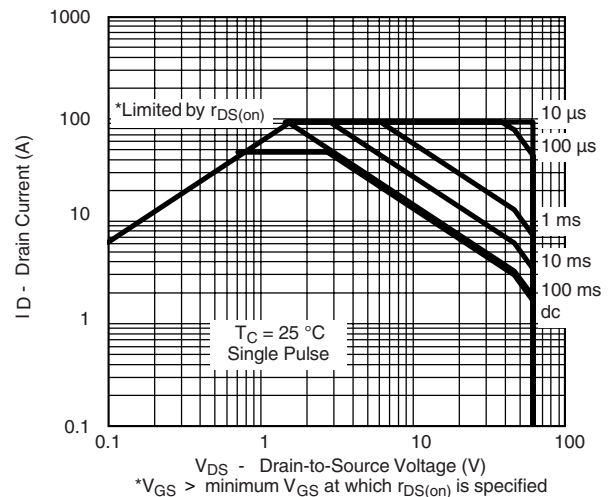
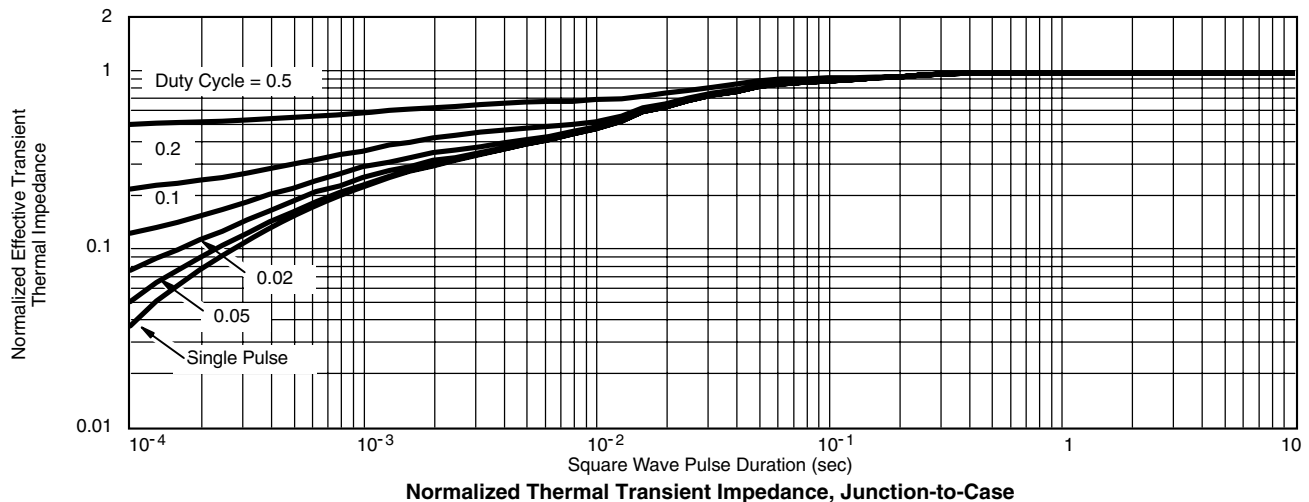
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****Transconductance****On-Resistance vs. Drain Current****Capacitance****Gate Charge**

**SUD50N06-08H**

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**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**On-Resistance vs. Junction Temperature****Source-Drain Diode Forward Voltage****THERMAL RATINGS****Maximum Avalanche Drain Current vs. Case Temperature****Safe Operating Area****Normalized Thermal Transient Impedance, Junction-to-Case**

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